

T:41-41

High Speed Back-Illuminated InGaAs PIN Photodiode

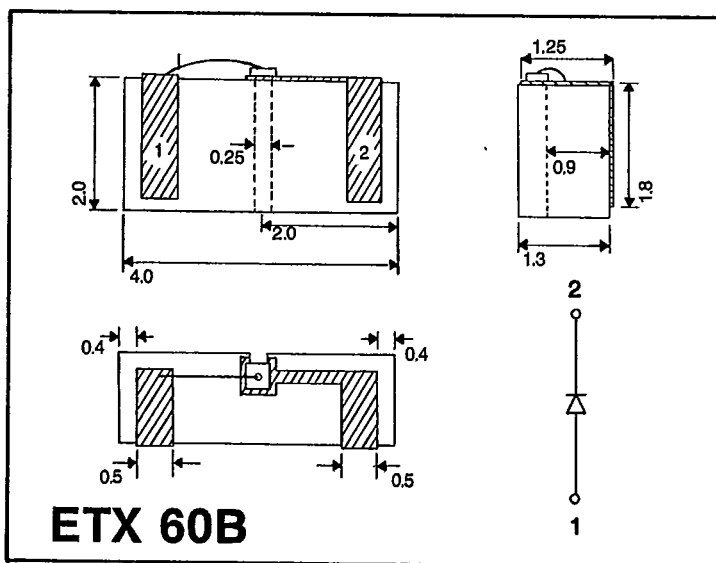
Description:

EPITAXX ETX 60B is a small area planar InGaAs photodiode mounted on a ceramic subcarrier. The device is illuminated through the substrate and its very low capacitance allows direct modulation at microwave frequencies.

Features:

- 60 μm active diameter
- grooved carrier
- optional custom submounts
- low dark current, low capacitance
- planar, passivated chip

Dimensions:



Maximum Ratings:

Parameter	Rating
Reverse Voltage	25V
Reverse Current	1mA
Forward Current	10mA
Operating Temperature	-40/+85C
Storage Temperature	-40/+100C

Optical/Electrical Characteristics (@ 25C)

Parameter	Conditions	Min	Typ	Max	Unit
Active Diameter			60		μm
Responsivity	$\lambda=1300\text{nm}$	0.70	0.80		A/W
Dark Current	$V_R=5\text{V}$		0.05	3	nA
Noise Current	$f=10\text{kHz}$		0.1		$\text{pA}/\sqrt{\text{Hz}}$
Total Capacitance	$V_R=5\text{V}$		0.3	0.5	pF
Bandwidth	$V_R=5\text{V}, 50\Omega, -3\text{dB}$		4000		MHz
Rise/Fall time	$V_R=5\text{V}, R_L=50\Omega$			0.08	nS

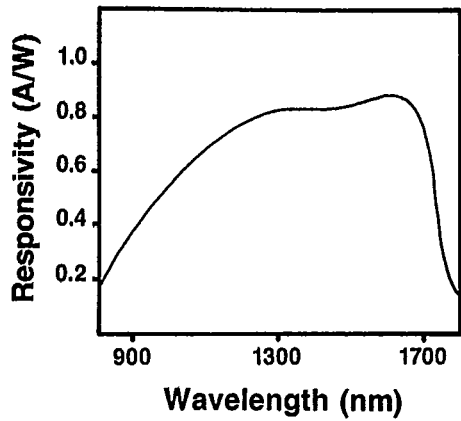
Corporate Headquarters

West Coast Sales Office

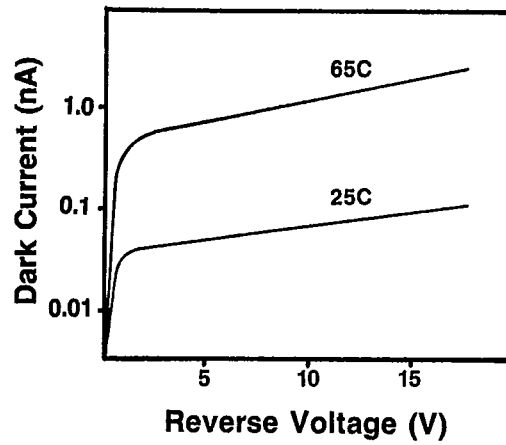
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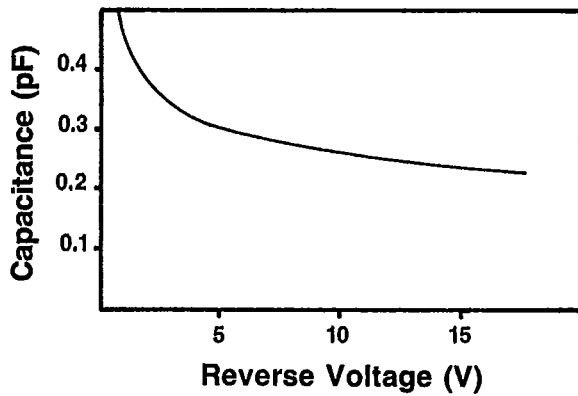
SPECTRAL RESPONSE



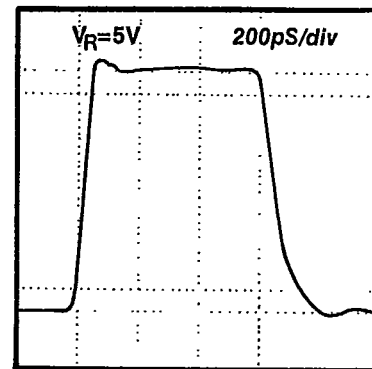
I-V CHARACTERISTIC



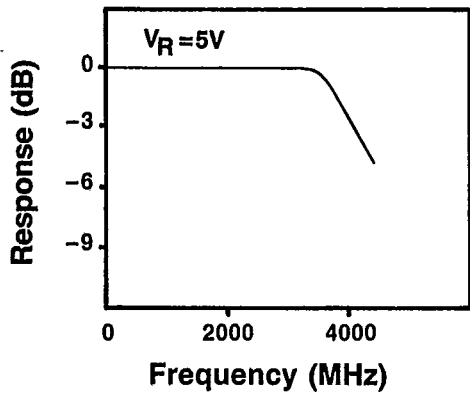
C-V CHARACTERISTIC



PULSE RESPONSE



BANDWIDTH



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